

**QUIZ NO. 1 - SOLUTION**

(Average score = 9.1/10 of those taking the quiz.)

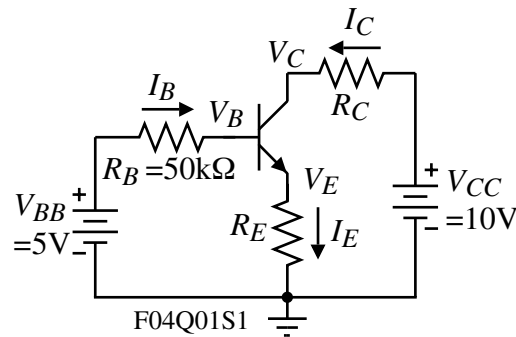
The npn BJT transistor shown has the parameter of  $\beta_F = 100$   
Assume that  $V_{BEQ} = 0.6V$ .

- a.) Assume the BJT transistor is in the forward active region and find the value of  $R_E$  that gives a collector current of 1mA.  
b.) What value of  $R_C$  will cause the base-collector junction to have zero volts (i.e., enter the saturation region for a BJT)?

Solution

(a.) The first step is to find a Thevenin equivalent circuit seen from the base to ground. This circuit is shown below where

$$V_{BB} = \frac{10 \cdot R_1}{R_1 + R_2} = 5V \quad (2) \quad \text{and} \quad R_B = R_1 \parallel R_2 = 50k\Omega \quad (2)$$



A collector current of 1mA implies that the base current,  $I_B = 10\mu A$ . The equation for the base current can be found from the base-emitter voltage loop and used to solve for  $R_E$ .

$$V_{BB} = I_B R_B + V_{BEQ} + I_B (1 + \beta_F) R_E \rightarrow (1 + \beta_F) R_E = \frac{V_{BB} - 0.6}{I_B} - R_B$$

$$101 R_E = \frac{4.4V}{10\mu A} - 50K = 440K - 50K = 390K \quad \rightarrow R_E = \frac{390K}{101} = \underline{3.86k\Omega} \quad (2)$$

(b.) Since  $V_{BC} = 0$ ,  $V_B = V_C$ . Thus, we need to first find  $V_B$ .

$$V_B = V_{BB} - I_B R_B = 5V - 10\mu A(50K) = 4.5V \quad (2)$$

$$\therefore R_C = \frac{V_{CC} - V_C}{I_C} = \frac{10 - 4.5}{1mA} = \underline{5.5k\Omega} \quad (2)$$

